

2SB1520

Preliminary

**Silicon PNP Epitaxial
High Voltage Amplifier****Features**

- Low saturation voltage
 $V_{CE}(\text{sat}) \leq -0.3 \text{ V}$
- Large current capacitance
 $I_C = -2 \text{ A}$

Table 1 Absolute Maximum Ratings
(Ta = 25°C)

Item	Symbol	Rating	Unit
Collector to base voltage	V _{CBO}	-80	V
Collector to emitter voltage	V _{CEO}	-80	V
Emitter to base voltage	V _{EBO}	-5	V
Collector current	I _C	-2	A
Peak collector current	i _{C(peak)*}	-3	A
Collector power dissipation	P _{C**}	1	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

* $P_W \leq 10 \text{ ms}$, duty cycle $\leq 20\%$

** When using the alumina ceramic board (12.5 × 20 × 0.7 mm)

Table 2 Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test condition
Collector to base breakdown voltage	V _{(BR)CBO}	-80	—	—	V	I _C = -10 μA, I _E = 0
Collector to emitter breakdown voltage	V _{(BR)CEO}	-80	—	—	V	I _C = -1 mA, R _{BE} = ∞
Emitter to base breakdown voltage	V _{(BR)EBO}	-5	—	—	V	I _C = -10 μA, I _E = 0
Collector cutoff current	I _{CBO}	—	—	-1	μA	V _{CB} = -65 V, I _E = 0
Collector cutoff current	I _{CEO}	—	—	-5	μA	V _{CE} = -65 V, R _{BE} = ∞
Emitter cutoff current	I _{EBO}	—	—	-1	μA	V _{EB} = -4 V, I _C = 0
DC current transfer ratio	h _{FE1}	120	—	300	—	V _{CE} = -2 V, I _C = -0.5 A*
DC current transfer ratio	h _{FE2}	40	—	—	—	V _{CE} = -2 V, I _C = -1.5 A*

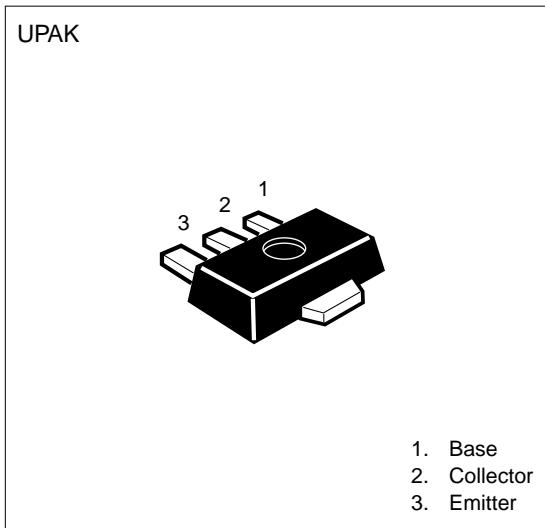


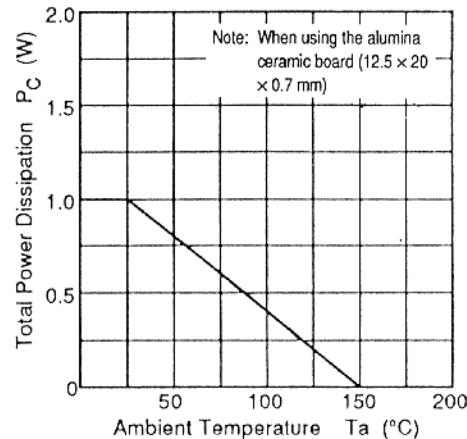
Table 2 Electrical Characteristics ($T_a = 25^\circ\text{C}$) (cont)

Item	Symbol	Min	Typ	Max	Unit	Test condition
Collector to emitter saturation voltage	$V_{CE(\text{sat})}$	—	—	-0.3	V	$I_C = -1 \text{ A}$, $I_B = -50 \text{ mA}$
Base to emitter saturation voltage	$V_{BE(\text{sat})}$	—	—	-1.2	V	$I_C = -1 \text{ A}$, $I_B = -50 \text{ mA}^*$

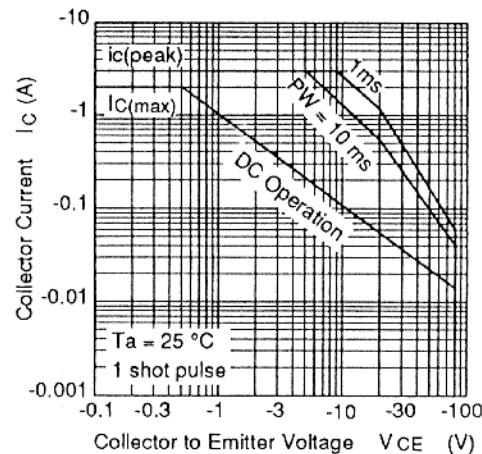
* Pulse test

** Marking is "GS".

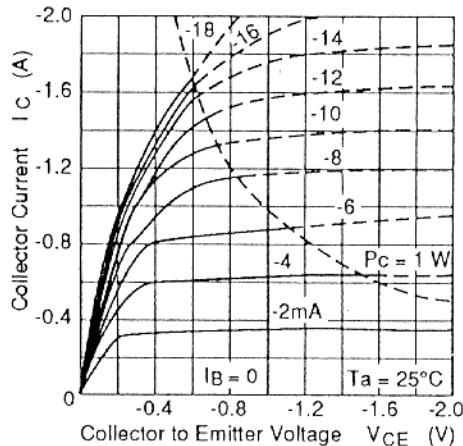
Maximum power dissipation curve



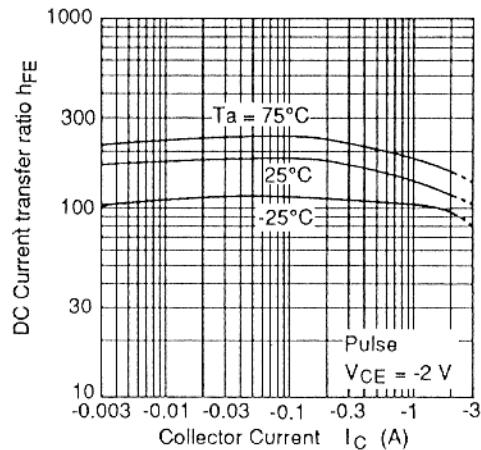
Area of safe operation



Typical transfer characteristics



DC Current transfer ratio vs. collector current



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